

NVBLS0D7N04M8

MOSFET – Power, Single, N-Channel

40 V, 240 A, 0.75 mΩ

Features

- Typical $R_{DS(on)}$ = 0.59 mΩ at V_{GS} = 10 V, I_D = 80 A
- Typical $Q_{g(tot)}$ = 144 nC at V_{GS} = 10 V, I_D = 80 A
- UIS Capability
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS T_J = 25°C unless otherwise noted

Parameter	Symbol	Ratings	Units
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	±20	V
Drain Current – Continuous (V_{GS} = 10) (Note 1)	I_D	240	A
Pulsed Drain Current T_C = 25°C		See Figure 4	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	737	mJ
Power Dissipation	P_D	357	W
Derate Above 25°C		2.38	W/°C
Operating and Storage Temperature	T_J, T_{STG}	–55 to +175	°C
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.42	°C/W
Maximum Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	43	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting T_J = 25°C, L = 0.36 mH, I_{AS} = 64 A, V_{DD} = 40 V during inductor charging and V_{DD} = 0 V during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2 oz copper.

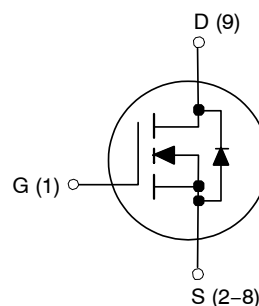


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MO-299A
CASE 100CU



ORDERING INFORMATION

Device	Package	Marking
NVBLS0D7N04M8TXG	MO-299A (Pb-Free)	0D7N04M8

NVBLS0D7N04M8

Table 1. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
B _V DSS	Drain-to-Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V		40	–	–	V
I _D SS	Drain-to-Source Leakage Current	V _{DS} = 40 V, V _{GS} = 0 V	T _J = 25°C	–	–	1	μA
			T _J = 175°C (Note 4)	–	–	1	mA
I _G SS	Gate-to-Source Leakage Current	V _{GS} = ±20 V		–	–	±100	nA
ON CHARACTERISTICS							
V _{GS} (th)	Gate-to-Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA		2.0	3.3	4.0	V
R _{DS} (on)	Drain-to-Source On Resistance	I _D = 80 A, V _{GS} = 10 V	T _J = 25°C	–	0.59	0.75	mΩ
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		–	12000	–	pF
C _{oss}	Output Capacitance			–	3300	–	pF
C _{rss}	Reverse Transfer Capacitance			–	440	–	pF
R _g	Gate Resistance	f = 1 MHz		–	3.3	–	Ω
Q _g (ToT)	Total Gate Charge at 10 V	V _{GS} = 0 to 10 V	V _{DD} = 32 V I _D = 80 A	–	144	188	nC
Q _g (th)	Threshold Gate Charge	V _{GS} = 0 to 2 V		–	22	26	nC
Q _{gs}	Gate-to-Source Charge			–	66	–	nC
Q _{gd}	Gate-to-Drain “Miller” Charge			–	16	–	nC
SWITCHING CHARACTERISTICS							
t _{on}	Turn-On Time	V _{DD} = 20 V, I _D = 80 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		–	–	162	ns
t _d (on)	Turn-On Delay			–	42	–	ns
t _r	Rise Time			–	73	–	ns
t _d (off)	Turn-Off Delay			–	83	–	ns
t _f	Fall Time			–	50	–	ns
t _{off}	Turn-Off Time			–	–	279	ns
DRAIN-SOURCE DIODE CHARACTERISTICS							
V _{SD}	Source-to-Drain Diode Voltage	I _{SD} = 80 A, V _{GS} = 0 V		–	–	1.25	V
		I _{SD} = 40 A, V _{GS} = 0 V		–	–	1.2	V
t _{rr}	Reverse-Recovery Time	I _F = 80 A, dI _{SD} /d _t = 100 A/μs, V _{DD} = 32 V		–	111	129	ns
Q _{rr}	Reverse-Recovery Charge			–	178	214	nC

4. The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production. Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Typical Characteristics

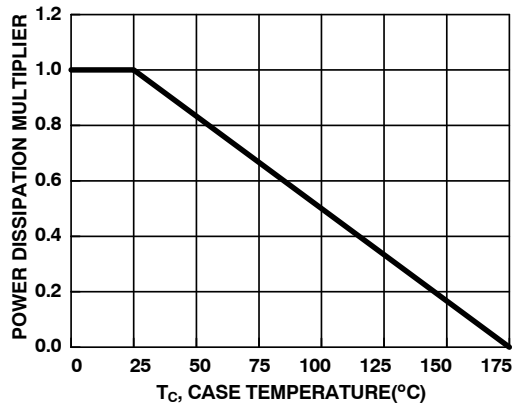


Figure 1. Normalized Power Dissipation vs. Case Temperature

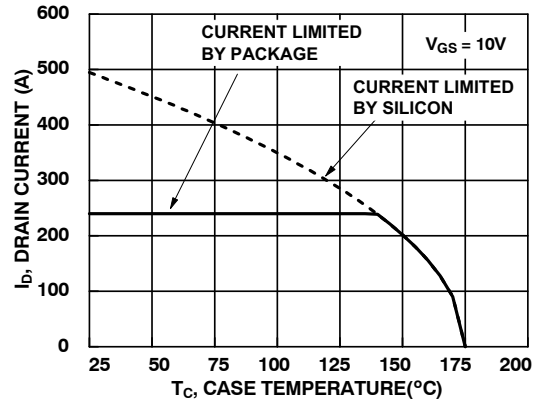


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

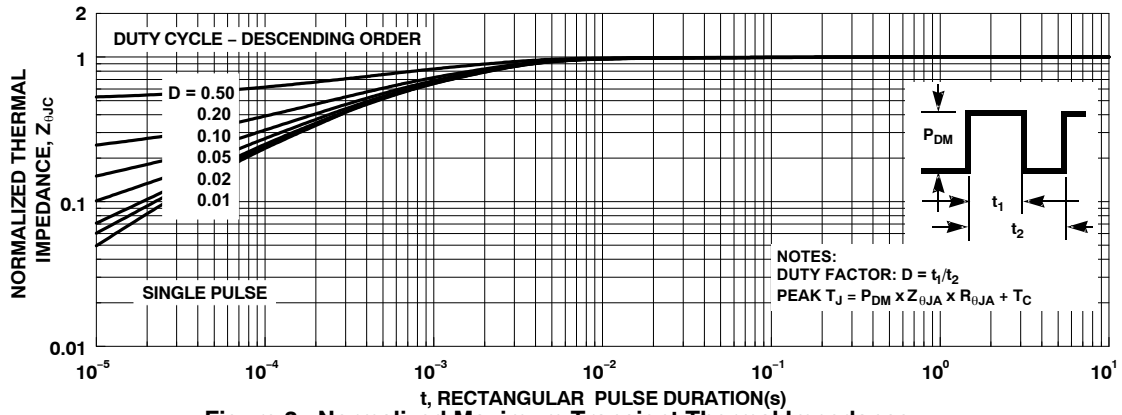


Figure 3. Normalized Maximum Transient Thermal Impedance

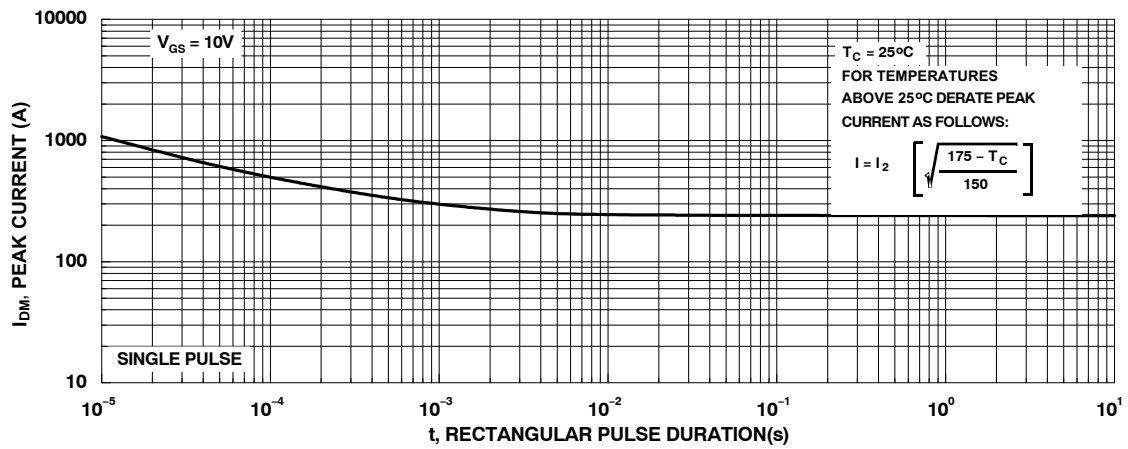


Figure 4. Peak Current Capability

Typical Characteristics

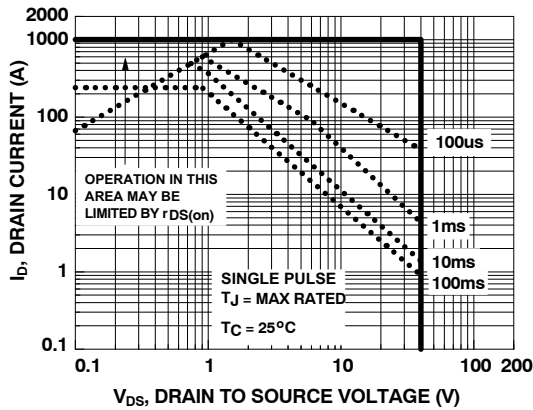
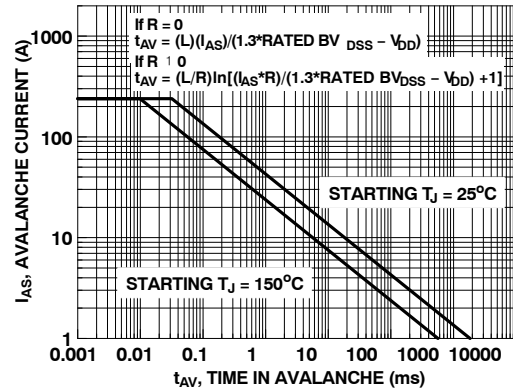


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

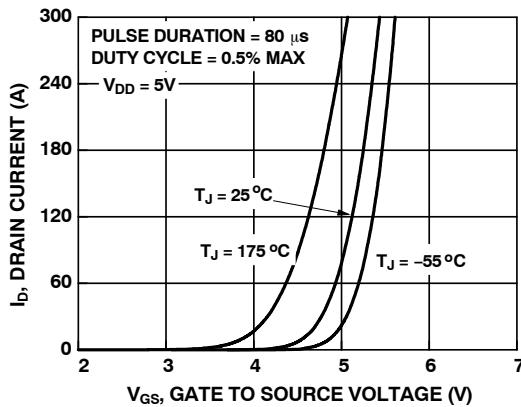


Figure 7. Transfer Characteristics

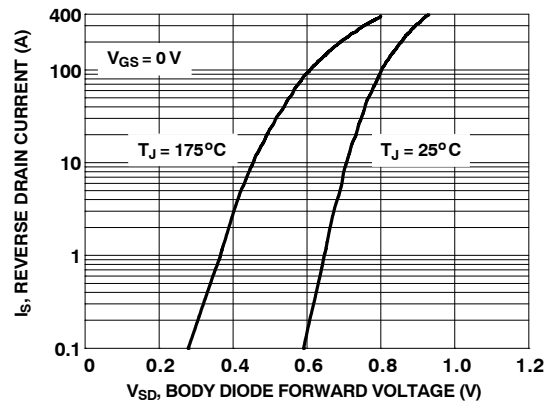


Figure 8. Forward Diode Characteristics

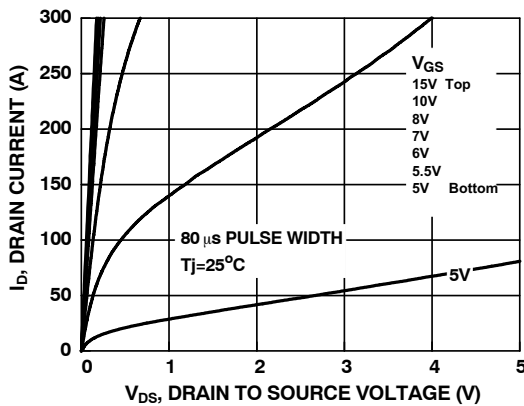


Figure 9. Saturation Characteristics

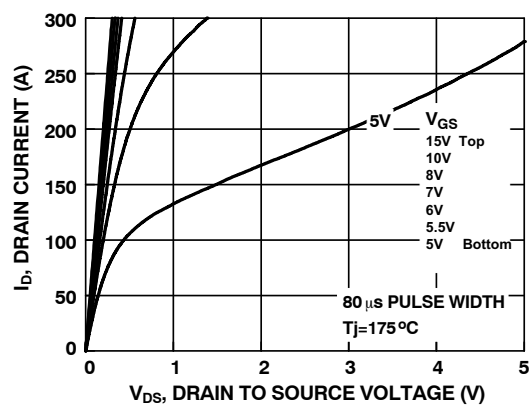


Figure 10. Saturation Characteristics

Typical Characteristics

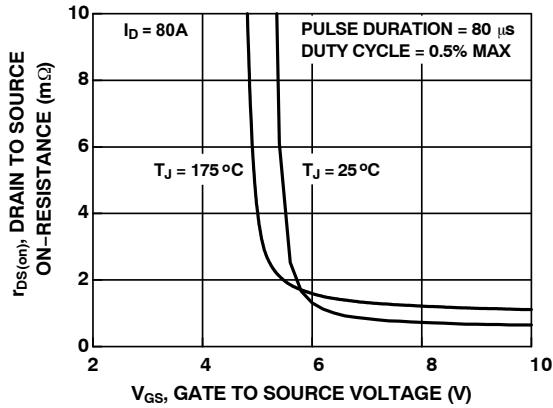


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

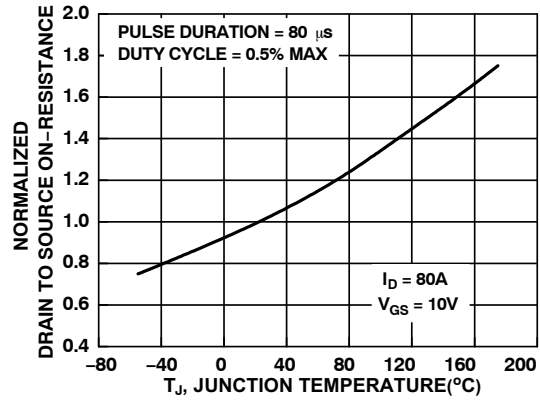


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

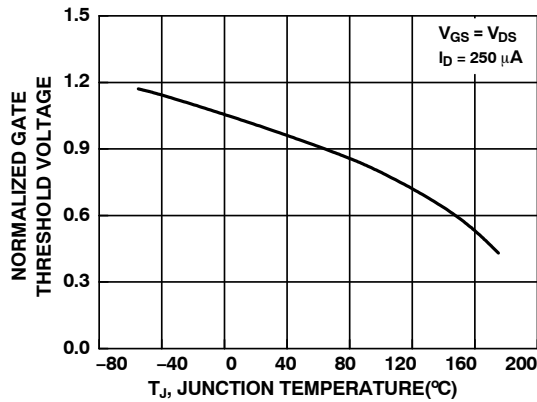


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

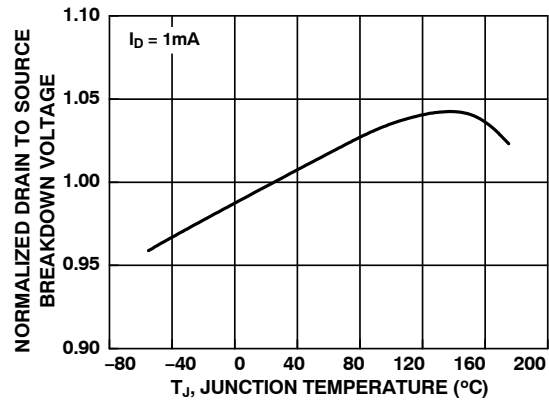


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

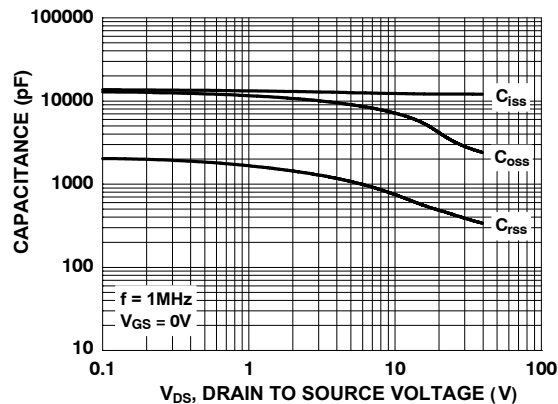


Figure 15. Capacitance vs. Drain to Source Voltage

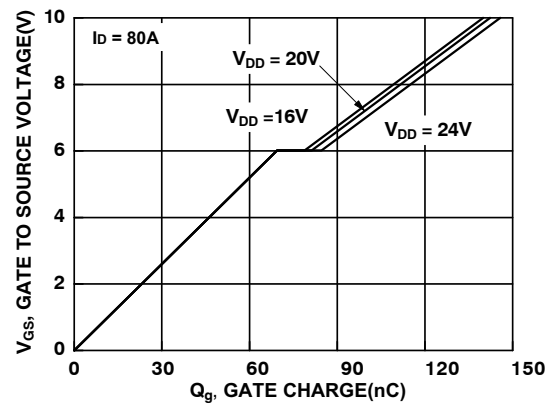
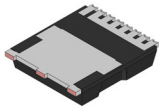
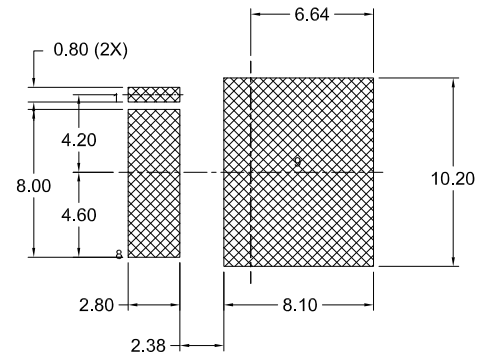
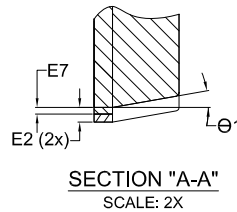
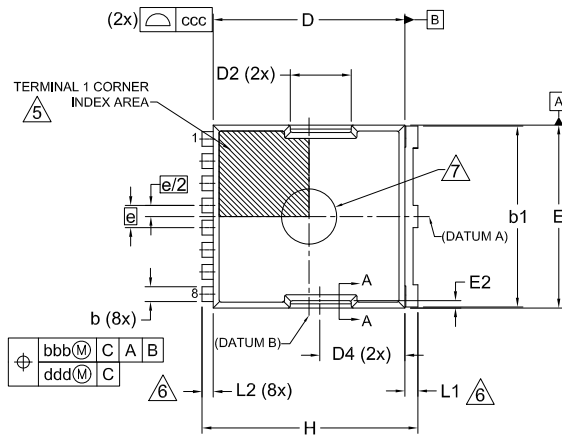


Figure 16. Gate Charge vs. Gate to Source Voltage

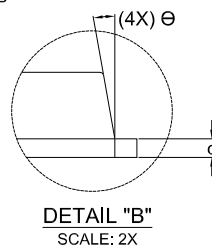
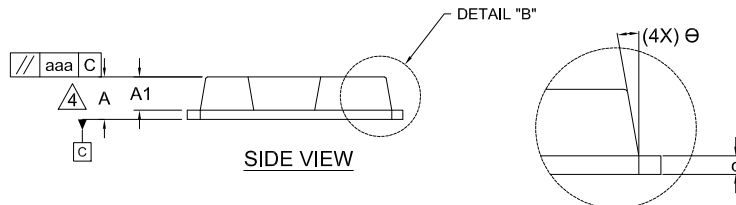


H-PSOF8L 11.68x9.80x2.30, 1.20P
CASE 100CU
ISSUE F

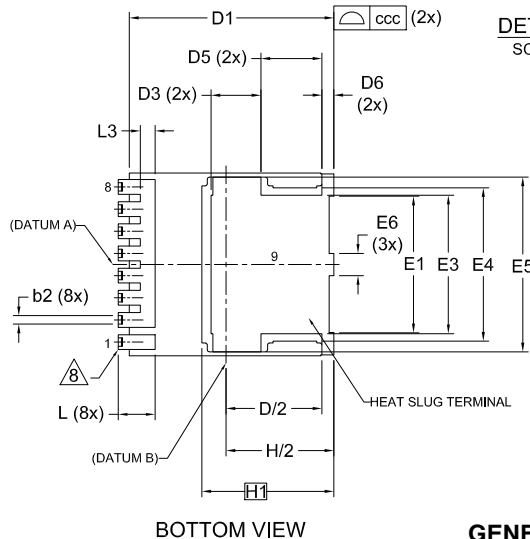
DATE 30 JUL 2024



*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

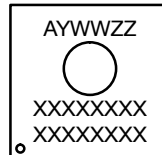


- NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
 3. "e" REPRESENTS THE TERMINAL PITCH.
 4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
 5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
 6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
 7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
 8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



GENERIC
MARKING DIAGRAM*

A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
XXXX = Specific Device Code



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.56
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
Θ	10° REF		
Θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

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